

TRANSITIONS BETWEEN POTENTIAL WELLS  
IN AMORPHOUS SEMICONDUCTORS  
INDUCED BY FREE CONDUCTION  
ELECTRONS

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S u m m a r y

We consider atomic transitions in the Anderson lattice in amorphous semiconductors accompanied by changing an atomic charge state. The conditions are calculated under which these transitions will depend not only on temperature but also on the excitation degree of the electron subsystem of a crystal. In this case, one could exert control over the Anderson lattice in amorphous semiconductors by using external actions (heating, irradiation, etc.).